DATA SHEET

NEC

SILICON POWER TRANSISTOR 2SA1008

PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1008 is a mold power transistor developed for high-speed switching, and is ideal for use as a driver in devices such as switching regulators, DC/DC converters, and high-frequency power amplifiers.

ORDERING INFORMATION

Part No.	Package		
2SA1008	TO-220AB		

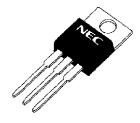
FEATURES

- · Low collector saturation voltage
- · Fast switching speed
- Complementary transistor: 2SC2331

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vсво		-100	V
Collector to emitter voltage	VCEO		-100	V
Emitter to base voltage	VEBO		-7.0	V
Collector current (DC)	IC(DC)		-2.0	А
Collector current (pulse)	C(pulse)	PW ≤ 300 <i>µ</i> s,	-4.0	Α
		duty cycle $\leq 10\%$		
Base current (DC)	B(DC)		-1.0	А
Total power dissipation	Р⊤	$Tc = 25^{\circ}C$	15	V
		$T_A = 25^{\circ}C$	1.5	W
Junction temperature	Tj		150	°C
Storage temperature	Tstg		-55 to +150	°C

(TO-220AB)



The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

ELECTRICAL CHARACTERISTICS (TA = 25°C)

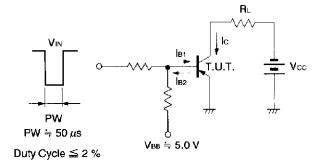
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to emitter voltage	VCEO(SUS)	Ic = –1.0 A, Iв1 = –0.1 A, L = 1 mH	-100			V
Collector to emitter voltage	VCEX(SUS)1	Ic = -1.0 A, I _{B1} = $-I_{B2}$ = -0.1 A, V _{BE(OFF)} = 5.0 V, L = 180 μ H, clamped	-100			V
Collector to emitter voltage	VCEX(SUS)2	Ic = -2.0 A, I _{B1} = -0.2 A, I _{B2} = 0.1 A, V _{BE(OFF)} = 5.0 V, L = 180 μ H, clamped	-100			V
Collector cutoff current	Ісво	$V_{CB} = -100 \text{ V}, \text{ IE} = 0 \text{ A}$			-10	μΑ
Collector cutoff current	ICER	$V_{CE} = -100 \text{ V}, \text{ R}_{BE} = 51 \Omega, \text{ T}_{A} = 125^{\circ}\text{C}$			-1.0	mA
Collector cutoff current	ICEX1	$V_{CE} = -100 \text{ V}, \text{ V}_{BE(OFF)} = 1.5 \text{ V}$			-10	μA
Collector cutoff current	ICEX2	$V_{CE} = -100 \text{ V}, \text{ V}_{BE(OFF)} = 1.5 \text{ V},$ TA = 125°C			-1.0	mA
Emitter cutoff current	Іево	$V_{EB} = -5.0 \text{ V}, \text{ Ic} = 0 \text{ A}$			-10	μA
DC current gain	hfe1	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -0.1 \text{ A}^{Note}$	40			
DC current gain	hfe2	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -1.0 \text{ A}^{Note}$	40		200	
Collector saturation voltage	V _{CE(sat)}	$I_{C} = -1.0 \text{ A}, I_{B} = -0.1 \text{ A}^{Note}$			-0.6	V
Base saturation voltage	V _{BE(sat)}	$I_{C} = -1.0 \text{ A}, I_{B} = -0.1 \text{ A}^{Note}$			-1.5	V
Turn-on time	ton	lc = −1.0 A, RL = 50 Ω,			0.5	μs
Storage time	tstg	$I_{B1} = -I_{B2} = -0.1 \text{ A}, \text{ Vcc} \cong -50 \text{ V}$			1.5	μs
Fall time	tr	Refer to the test circuit.			0.5	μs

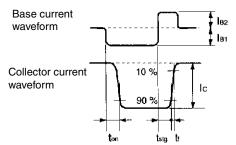
Note Pulse test PW \leq 350 μ s, duty cycle \leq 2%

hFE CLASSIFICATION

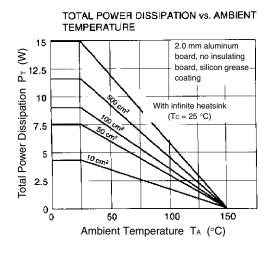
Marking	М	L	К
hfe2	40 to 80	60 to 120	100 to 200

SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT

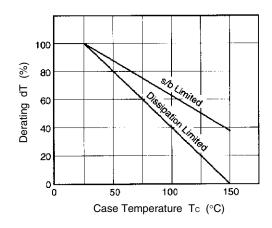




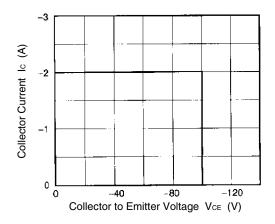




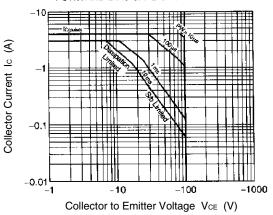
DERATING CURVE OF SAFE OPERATING AREA

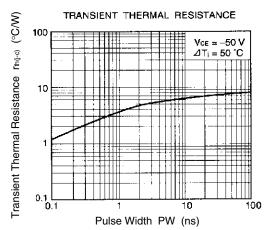


REVERSE BIAS SAFE OPERATING AREA

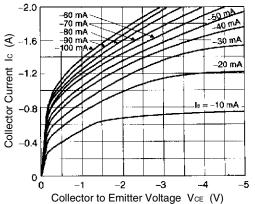


FORWARD BIAS SAFE OPERATING AREA



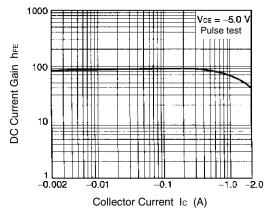


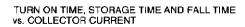
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

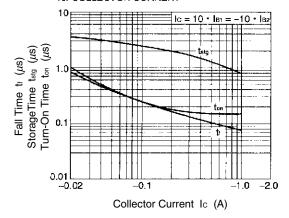


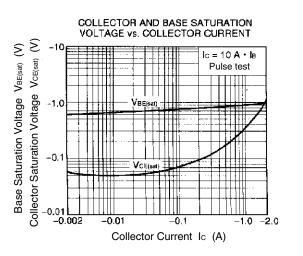
www.agelectronica.com www.agelectronica.com

DC CURRENT GAIN vs. COLLECTOR CURRENT





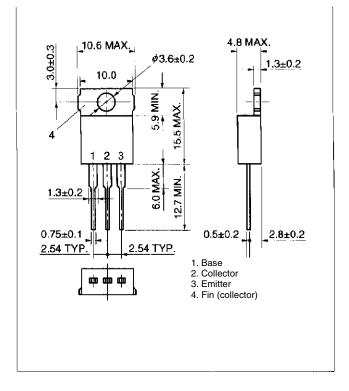




www.agelectronica.com www.agelectronica.com

PACKAGE DRAWING (UNIT: mm)

TO-220AB (MP-25)



- The information in this document is current as of July, 2001. The information is subject to change without notice. For actual design-in, refer to the latest publications of NEC's data sheets or data books, etc., for the most up-to-date specifications of NEC semiconductor products. Not all products and/or types are available in every country. Please check with an NEC sales representative for availability and additional information.
- No part of this document may be copied or reproduced in any form or by any means without prior written consent of NEC. NEC assumes no responsibility for any errors that may appear in this document.
- NEC does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from the use of NEC semiconductor products listed in this document or any other liability arising from the use of such products. No license, express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC or others.
- Descriptions of circuits, software and other related information in this document are provided for illustrative purposes in semiconductor product operation and application examples. The incorporation of these circuits, software and information in the design of customer's equipment shall be done under the full responsibility of customer. NEC assumes no responsibility for any losses incurred by customers or third parties arising from the use of these circuits, software and information.
- While NEC endeavours to enhance the quality, reliability and safety of NEC semiconductor products, customers
 agree and acknowledge that the possibility of defects thereof cannot be eliminated entirely. To minimize
 risks of damage to property or injury (including death) to persons arising from defects in NEC
 semiconductor products, customers must incorporate sufficient safety measures in their design, such as
 redundancy, fire-containment, and anti-failure features.
- NEC semiconductor products are classified into the following three quality grades:

"Standard", "Special" and "Specific". The "Specific" quality grade applies only to semiconductor products developed based on a customer-designated "quality assurance program" for a specific application. The recommended applications of a semiconductor product depend on its quality grade, as indicated below. Customers must check the quality grade of each semiconductor product before using it in a particular application.

- "Standard": Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
- "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
- "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

The quality grade of NEC semiconductor products is "Standard" unless otherwise expressly specified in NEC's data sheets or data books, etc. If customers wish to use NEC semiconductor products in applications not intended by NEC, they must contact an NEC sales representative in advance to determine NEC's willingness to support a given application.

(Note)

- (1) "NEC" as used in this statement means NEC Corporation and also includes its majority-owned subsidiaries.
- (2) "NEC semiconductor products" means any semiconductor product developed or manufactured by or for NEC (as defined above).

M8E 00.4